

## OptiMOS® -T2 Power-Transistor



### Product Summary

$V_{DS}$	55	V
$R_{DS(on),max}$ (SMD version)	3.5	m $\Omega$
$I_D$	100	A

### Features

- N-channel - Enhancement mode
- Automotive AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green product (RoHS compliant)
- 100% Avalanche tested

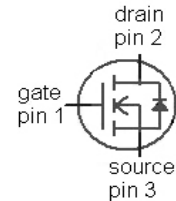
PG-TO263-3-2

PG-TO262-3-1

PG-TO220-3-1



Type	Package	Marking
IPB100N06S3L-04	PG-TO263-3-2	3PN06L04
IPI100N06S3L-04	PG-TO262-3-1	3PN06L04
IPP100N06S3L-04	PG-TO220-3-1	3PN06L04



**Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current <sup>1)</sup>	$I_D$	$T_C=25\text{ }^\circ\text{C}$ , $V_{GS}=10\text{ V}$	100	A
		$T_C=100\text{ }^\circ\text{C}$ , $V_{GS}=10\text{ V}^2)$	100	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25\text{ }^\circ\text{C}$	400	
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	$I_D=50\text{ A}$	1090	mJ
Avalanche current, single pulse	$I_{AS}$		100	A
Gate source voltage <sup>3)</sup>	$V_{GS}$		$\pm 16$	V
Power dissipation	$P_{tot}$	$T_C=25\text{ }^\circ\text{C}$	214	W
Operating and storage temperature	$T_j$ , $T_{stg}$		-55 ... +175	$^\circ\text{C}$
IEC climatic category; DIN IEC 68-1			55/175/56	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Thermal characteristics<sup>2)</sup>**

Thermal resistance, junction - case	$R_{thJC}$		-	-	0.7	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$		-	-	62	
SMD version, device on PCB	$R_{thJA}$	minimal footprint	-	-	62	
		6 cm <sup>2</sup> cooling area <sup>4)</sup>	-	-	40	

**Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**
**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	55	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=150\text{ }\mu\text{A}$	1.2	1.6	2.2	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	0.01	1	$\mu\text{A}$
		$V_{DS}=55\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ }^\circ\text{C}^{2)}$	-	1	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=16\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=5\text{ V}, I_D=59\text{ A}$	-	4.9	6.2	m $\Omega$
		$V_{GS}=5\text{ V}, I_D=59\text{ A},$ SMD version	-	4.6	5.9	
		$V_{GS}=10\text{ V}, I_D=80\text{ A}$	-	3.1	3.8	
		$V_{GS}=10\text{ V}, I_D=80\text{ A},$ SMD version	-	2.8	3.5	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

### Dynamic characteristics<sup>2)</sup>

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	17270	-	pF
Output capacitance	$C_{oss}$		-	2165	-	
Reverse transfer capacitance	$C_{rss}$		-	2070	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=27.5\text{ V},$ $V_{GS}=10\text{ V}, I_D=80\text{ A},$ $R_G=2\ \Omega$	-	30	-	ns
Rise time	$t_r$		-	58	-	
Turn-off delay time	$t_{d(off)}$		-	82	-	
Fall time	$t_f$		-	55	-	

### Gate Charge Characteristics<sup>2)</sup>

Gate to source charge	$Q_{gs}$	$V_{DD}=11\text{ V}, I_D=80\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	71	-	nC
Gate to drain charge	$Q_{gd}$		-	45	-	
Gate charge total	$Q_g$		-	241	362	
Gate plateau voltage	$V_{plateau}$		-	3.8	-	V

### Reverse Diode

Diode continuous forward current <sup>2)</sup>	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	100	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$		-	-	400	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=80\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	0.6	0.9	1.3	V
Reverse recovery time <sup>2)</sup>	$t_{rr}$	$V_R=27.5\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	95	-	ns
Reverse recovery charge <sup>2)</sup>	$Q_{rr}$		-	135	-	

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC} = 0.7\text{ K/W}$  the chip is able to carry 176 A at 25°C. For detailed information see Application Note ANPS071E

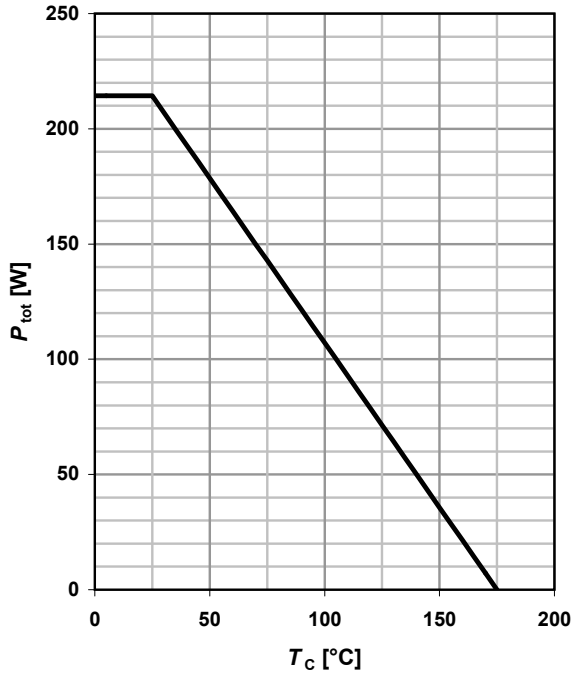
<sup>2)</sup> Defined by design. Not subject to production test.

<sup>3)</sup> Qualified at -5V and +16V.

<sup>4)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

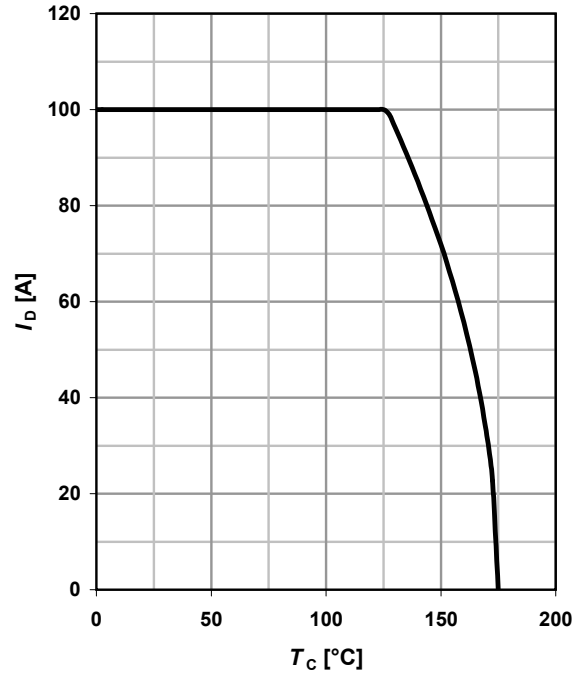
**1 Power dissipation**

$P_{tot}=f(T_C); V_{GS} \geq 4\text{ V}$



**2 Drain current**

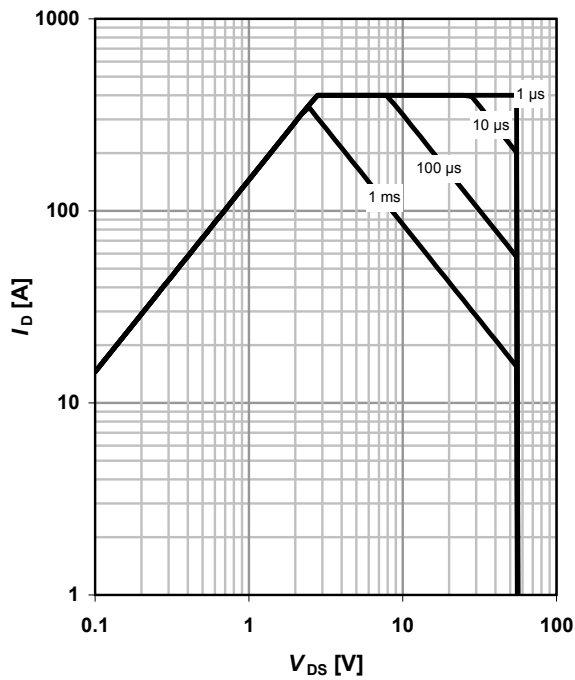
$I_D=f(T_C); V_{GS} \geq 4\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

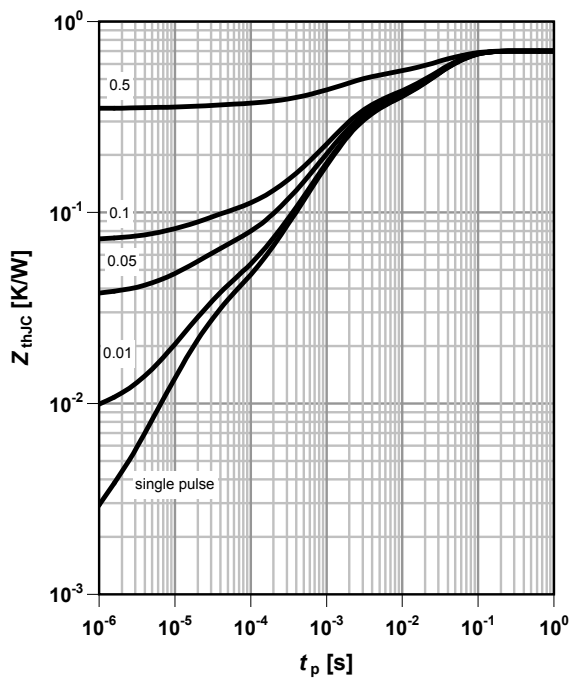
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

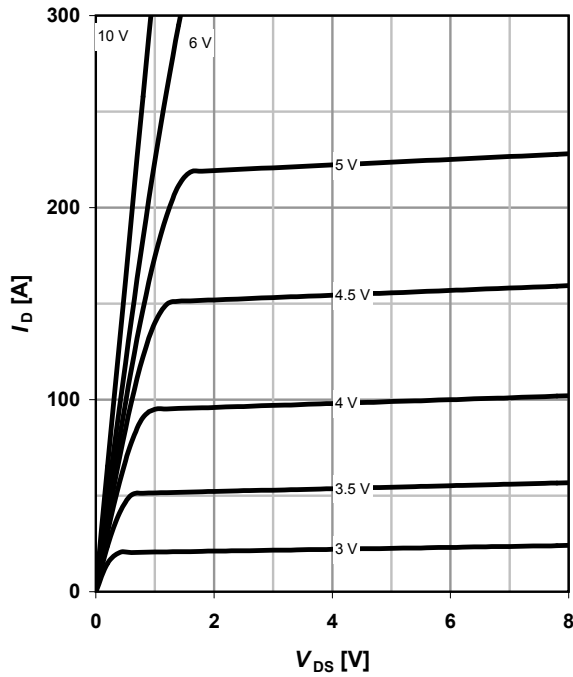
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

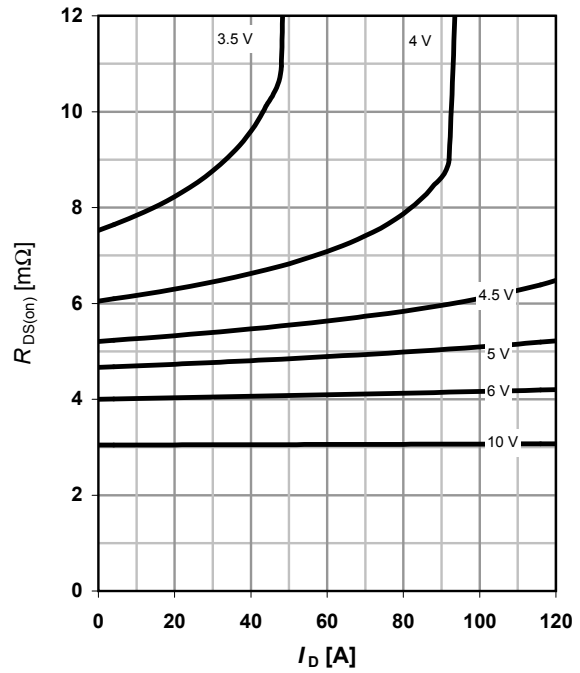
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

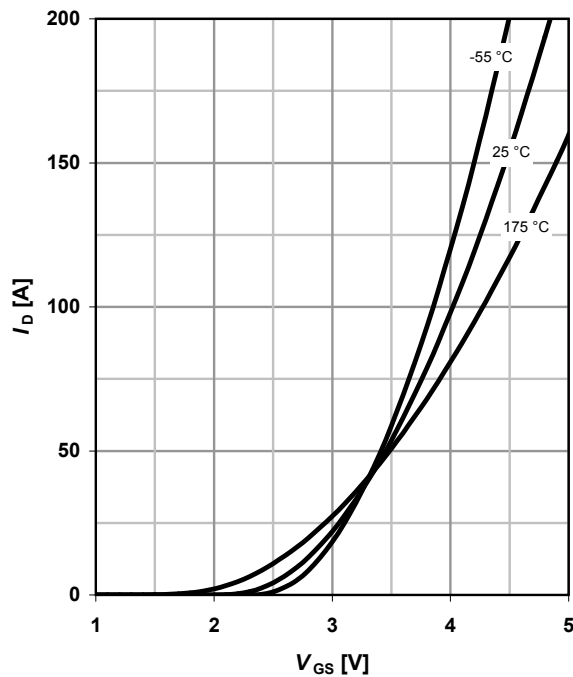
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

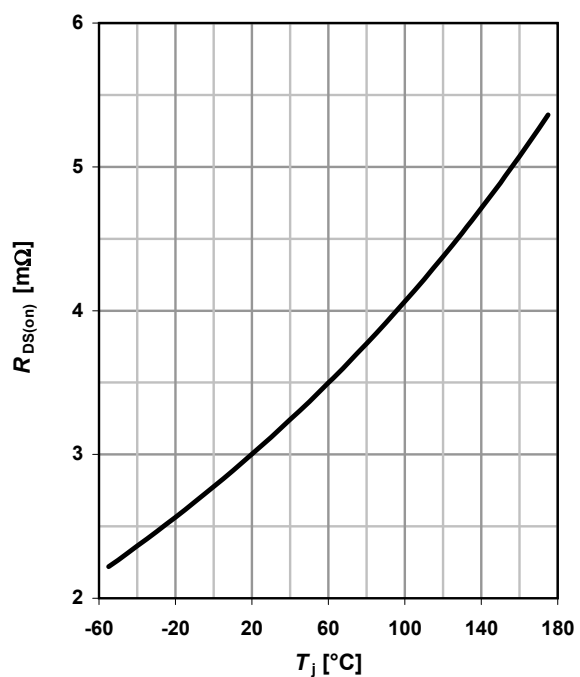
$I_D = f(V_{GS}); V_{DS} = 4\text{ V}$

parameter:  $T_j$



**8 Typ. drain-source on-state resistance**

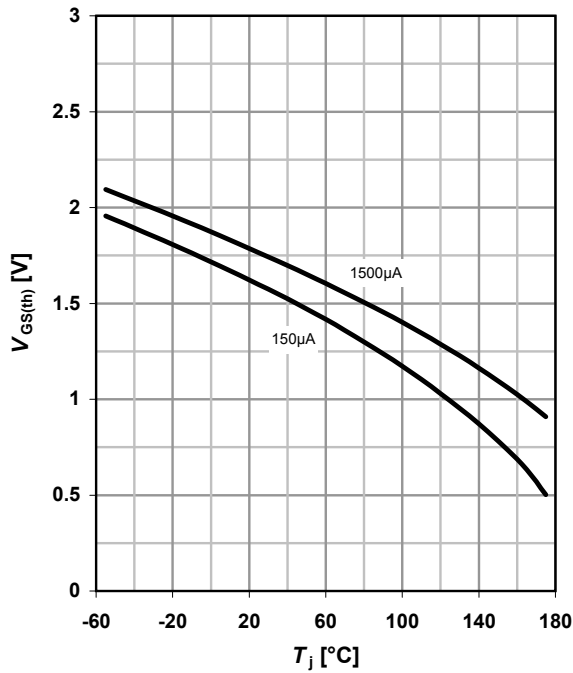
$R_{DS(on)} = f(T_j); I_D = 80\text{ A}; V_{GS} = 10\text{ V}$



**9 Typ. gate threshold voltage**

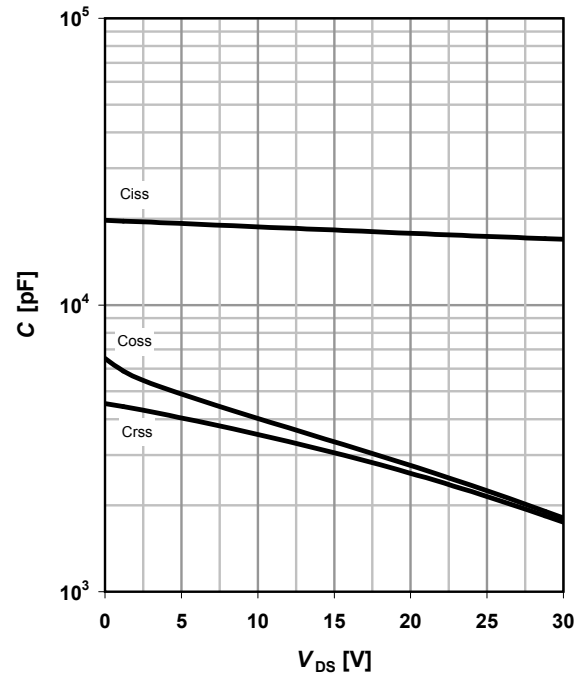
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**10 Typ. capacitances**

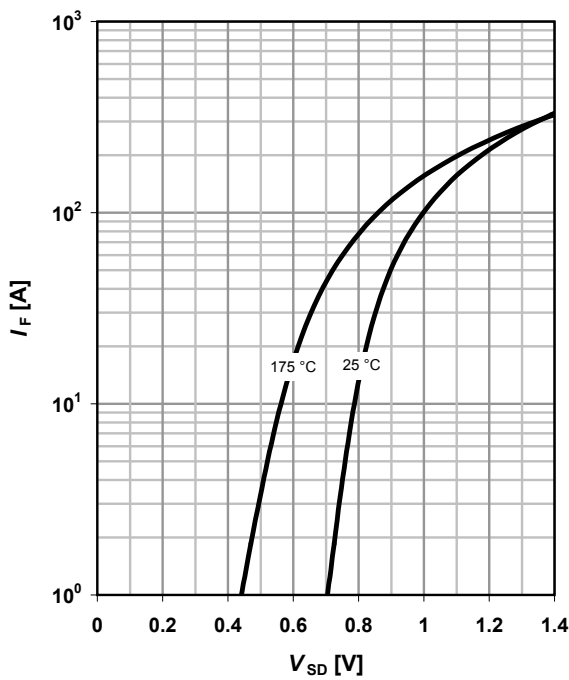
$C = f(V_{DS}); V_{GS} = 0 V; f = 1 MHz$



**11 Typical forward diode characteristics**

$I_F = f(V_{SD})$

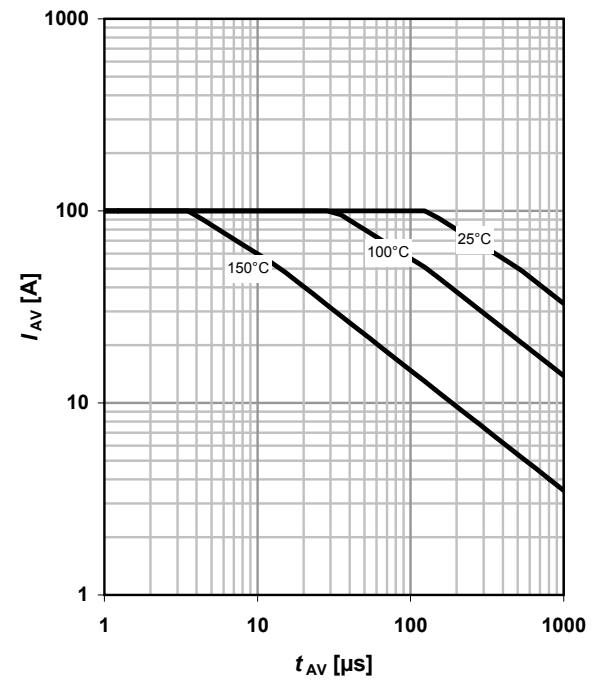
parameter:  $T_j$



**12 Typ. avalanche characteristics**

$I_{AV} = f(t_{AV})$

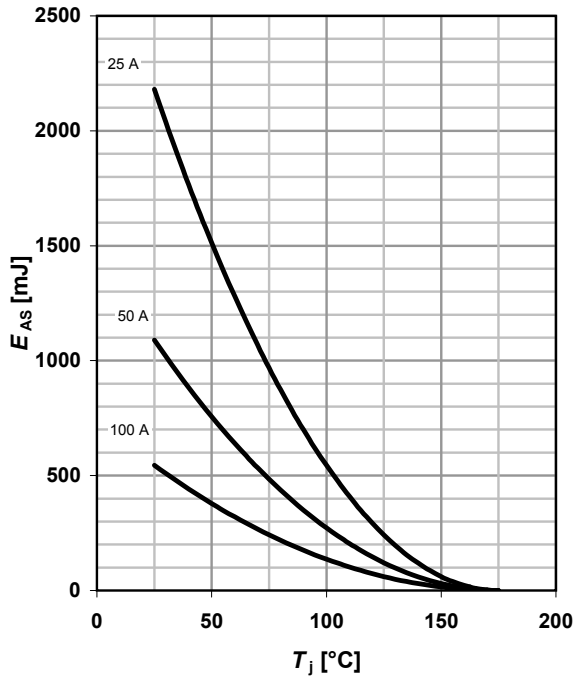
parameter:  $T_{j(start)}$



**13 Typical avalanche energy**

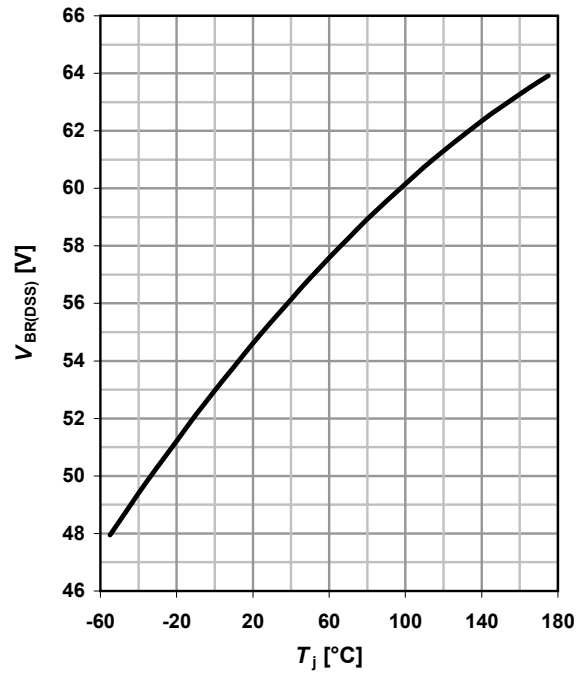
$E_{AS} = f(T_j)$

parameter:  $I_D$



**14 Drain-source breakdown voltage**

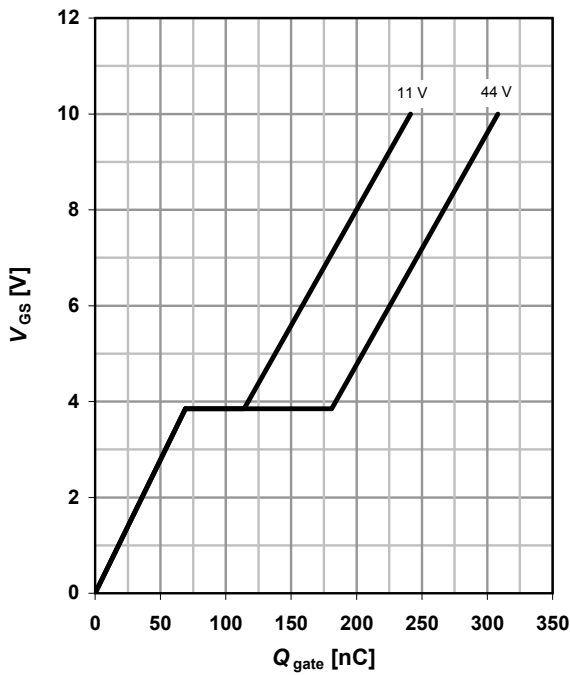
$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$



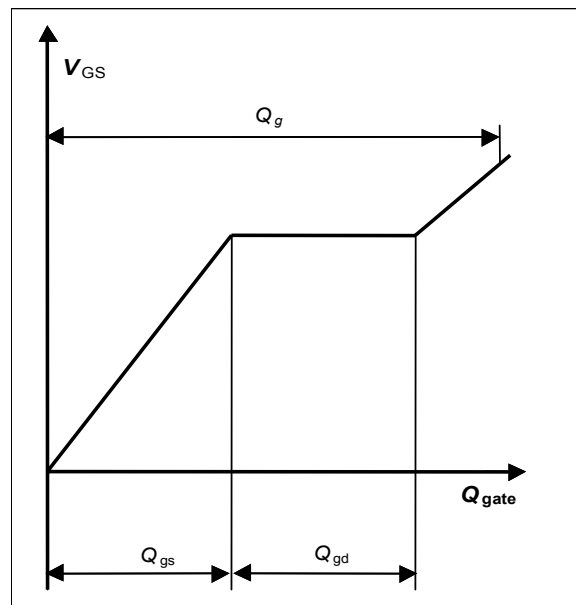
**15 Typ. gate charge**

$V_{GS} = f(Q_{gate}); I_D = 80 \text{ A pulsed}$

parameter:  $V_{DD}$



**16 Gate charge waveforms**



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Revision History

Version	Date	Changes
Data Sheet 2.1	15.12.2006	Removal of ordering code
Data Sheet 2.1	15.12.2006	Implementation of avalanche current single pulse
Data Sheet 2.1	15.12.2006	Update of Infineon address
Data Sheet 2.1	15.12.2006	Removal of foot note 3, avalanche diagrams
Data Sheet 2.1	15.12.2006	Implementation of Qrr and trr typ
Data Sheet 2.1	15.12.2006	Update of disclaimer
Data Sheet 2.1	15.12.2006	Implementation of RoHS and AEC logo, update of feature list
Data Sheet 1.1	07.11.2007	Update of data sheet layout
Data Sheet 1.1	07.11.2007	Adaptation of Ias from 200A to 100A
Data Sheet 1.1	07.11.2007	implementation of footnote 2 for Eas specification
Data Sheet 1.1	07.11.2007	removal of Vdg specification from data sheet